



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Handwritten: 2/1/03
#20/c
1/14/02

In re Patent Application of
Hisashi OHTANI et al. ✓
Serial No. 09/593,765 ✓
Filed: June 14, 2000 ✓
For: SEMICONDUCTOR DEVICE
COMPRISING FIRST INSULATING FILM,
SECOND INSULATING FILM COMPRISING
ORGANIC RESIN ON THE FIRST
INSULATING FILM, AND PIXEL ELECTRODE)
OVER THE SECOND INSULATING FILM)

) Art Unit: 2811 ✓
) Examiner: C. Nguyen ✓

CERTIFICATE OF MAILING	
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AMENDMENT

Honorable Commissioner of Patents
Washington, D.C. 20231

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Sir:

In response to the Office Action dated August 26, 2002 please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 1, 3, 8, 10, 15, 17, 23, 25, 31, 33, 36, 38, 42, 44, 48 and 50 as follows:

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1. (Amended) A semiconductor device comprising:
a semiconductor layer having at least first and second impurity regions and a channel region formed on an insulating surface;
a gate insulating film adjacent to said semiconductor layer;
a gate electrode adjacent to said gate insulating film;
a first inorganic insulating film covering at least said gate electrode and said semiconductor layer except for contact holes opened therein;